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With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

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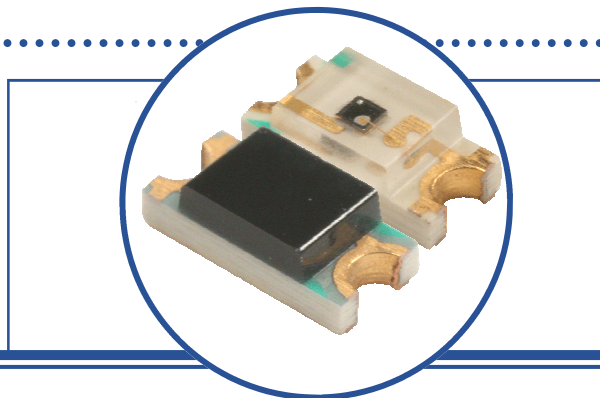
Silicon Photo Darlington in Miniature 1206 SMD Package

OP520DA, OP521DA



Features:

- High Photo Sensitivity
- Fast Response Time
- 1206 Package Size
- Opaque or Water Clear Flat Lens
- High Current Gain



Descriptions:

The **OP520DA** and **OP521DA** are NPN silicon photo darlington mounted in miniature 1206 SMD packages. Both the **OP520DA** and **OP521DA** have a flat lens however, the **OP520DA** lens are opaque to shield the device from ambient light unlike the lens of the **OP521DA**. These sensors are packaged in compact 1206 size chip carriers that are compatible with most automated mounting equipment. The **OP520DA** and **OP521DA** are mechanically and spectrally matched to the OP250 series infrared LEDs.

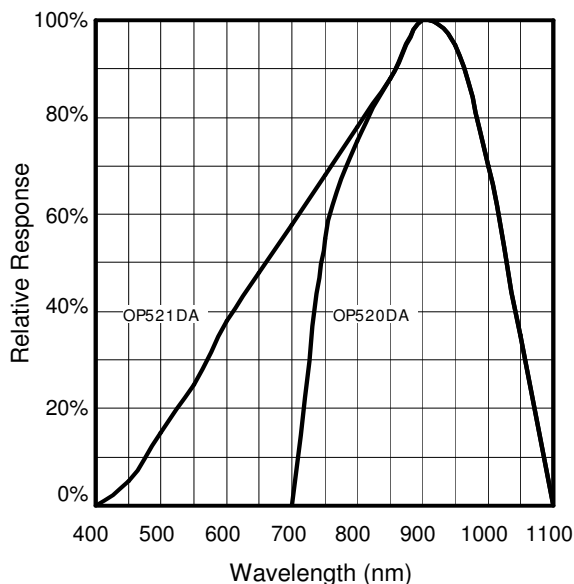
Since these devices have a flat window lens, they enable a wide acceptance angle. It is packaged in a plastic leadless chip carrier which is compatible for new applications with that need smaller dimension packages for automated mounting and detection equipment with new innovative designs. **OP520DA** and **OP521DA** are 100% production tested using infrared light for close correlation with Optek GaAs and GaAlAs emitters. Photo darlington devices are normally used in application where light signals are low and more current gain is needed than in comparison to the standard phototransistors.

Applications

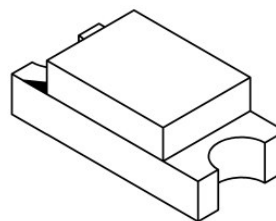
- Non-Contact Position Sensing
- Datum detection
- Machine automation
- Optical encoders

Ordering Information			
Part Number	Sensor	Viewing Angle	Lead Length
OP520DA	Photo Darlington	150°	N/A
OP521DA	Photo Darlington		

Relative Response vs. Wavelength



OP520DA, OP521DA



Optek reserves the right to make changes at any time in order to improve design and to supply the best product possible.

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Absolute Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise noted

Storage Temperature Range	-40° C to +100° C
Operating Temperature Range	-25° C to +85° C
Lead Soldering Temperature	260° C ⁽¹⁾
Collector-Emitter Voltage	35V
Emitter-Collector Voltage	5 V
Collector Current	30 mA
Power Dissipation	100 mW ⁽²⁾

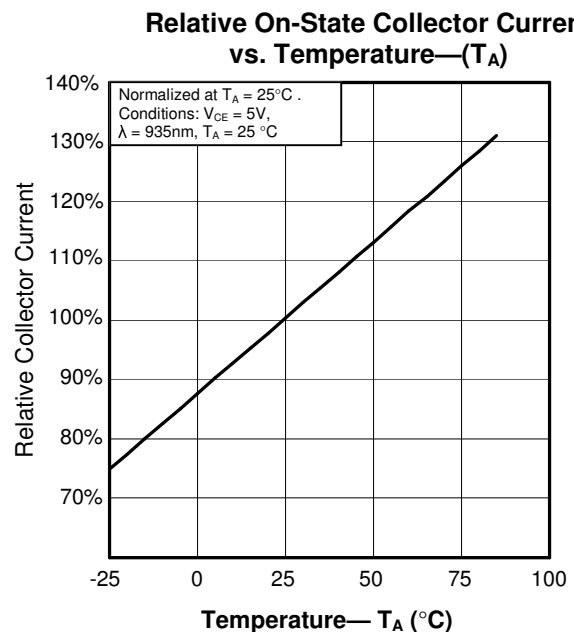
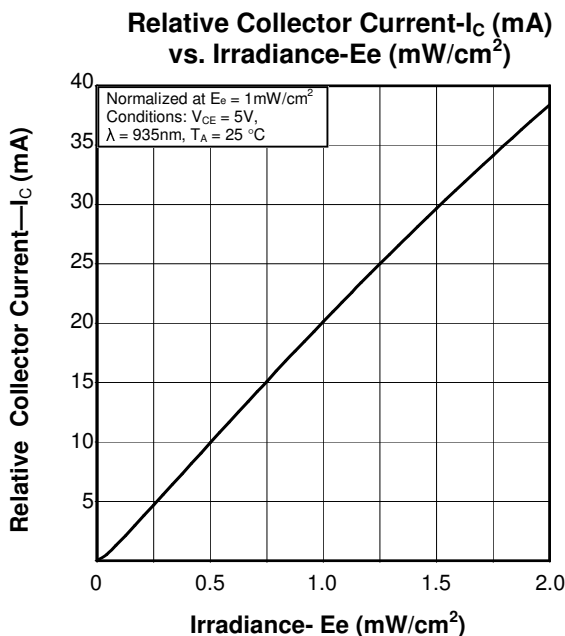
Notes:

- Solder time less than 5 seconds at temperature extreme.
- De-rate linearly at 2.17 mW/°C above 25° C.

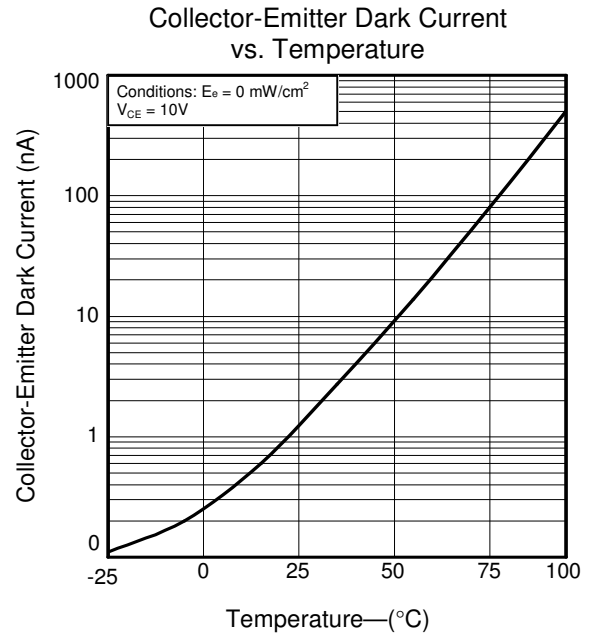
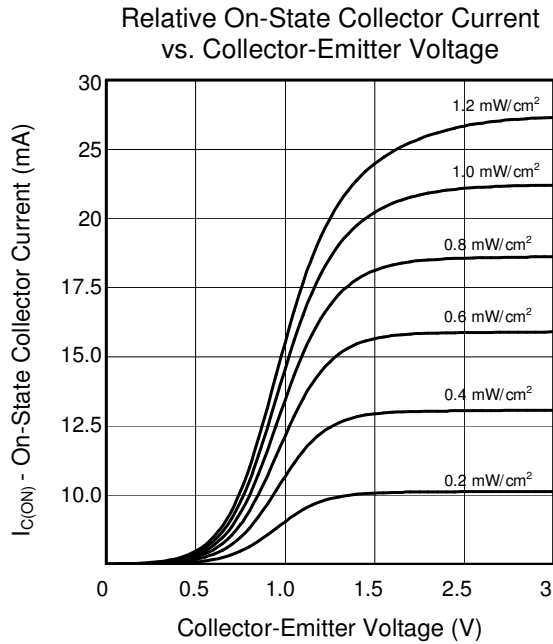
Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)

SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	CONDITIONS
$I_{C(ON)}$	On-State Collector Current	10.0			mA	$V_{CE} = 5.0V, E_e = 0.5\text{mW/cm}^2$ ⁽³⁾
$V_{CE(SAT)}$	Collector-Emitter Saturation Voltage			1.7	V	$I_C = 1\text{mA}, E_e = 5.0\text{mW/cm}^2$ ⁽³⁾
I_{CEO}	Collector-Emitter Dark Current			200	nA	$V_{CE} = 5.0V, E_e = 0$ ⁽⁴⁾
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	35			V	$I_C = 100\mu\text{A}, E_e = 0$
$V_{(BR)ECO}$	Emitter-Collector Breakdown Voltage	5			V	$I_E = 100\mu\text{A}, E_e = 0$
λ	Spectral range of sensitivity					$V_{CE} = 5.0V$
	OP521DA	400		1100	nm	
	OP520DA	700		1100	nm	
t_r, t_f	Rise and Fall Times		50		μs	$I_C = 1\text{mA}, R_L = 1K\Omega$

- Light source is an unfiltered GaAs LED with a peak emission wavelength of 935nm and a radiometric intensity level which varies less than 10% over the entire lens surface of the photo darlington being tested.
- To Calculate typical collector dark current in μA , use the formula $I_{CEO} = 10^{(0.04 T_A - 3/4)}$ where T_A is the ambient temperature in °C.

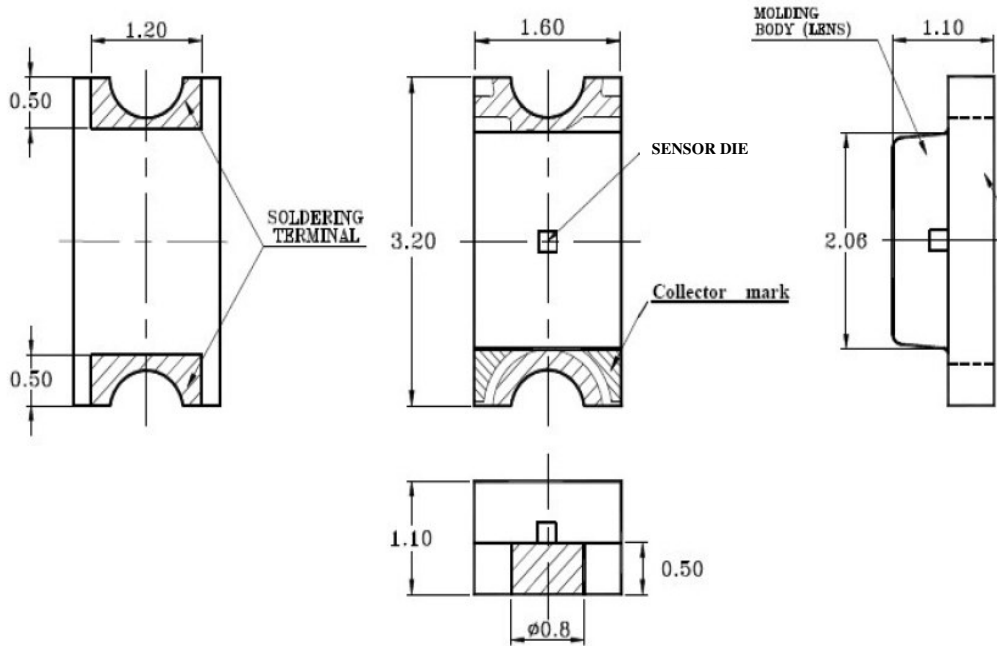


OP520DA, OP521DA

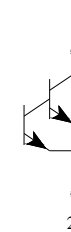


**Silicon Photo Darlington in Miniature 1206 SMD
Package**
OP520DA, OP521DA

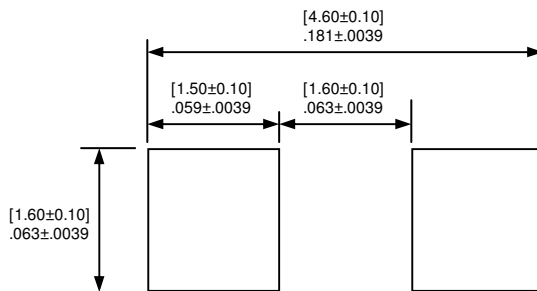
Package Dimensions



OP520DA, OP521DA



RECOMMENDED SOLDER PADS



PIN	FUNCTION
1	Collector
2	Emitter